



Welcome to [E-XFL.COM](#)

Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	416
Number of Logic Elements/Cells	4160
Total RAM Bits	53248
Number of I/O	93
Number of Gates	263000
Voltage - Supply	2.375V ~ 2.625V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	144-LQFP
Supplier Device Package	144-TQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep20k100cf144c7

...and More Features

- Low-power operation design
 - 1.8-V supply voltage (see Table 2)
 - Copper interconnect reduces power consumption
 - MultiVolt™ I/O support for 1.8-V, 2.5-V, and 3.3-V interfaces
 - ESBs offering programmable power-saving mode
- Flexible clock management circuitry with up to four phase-locked loops (PLLs)
 - Built-in low-skew clock tree
 - Up to eight global clock signals
 - ClockLock™ feature reducing clock delay and skew
 - ClockBoost™ feature providing clock multiplication and division
 - ClockShift™ feature providing programmable clock phase and delay shifting
- Powerful I/O features
 - Compliant with peripheral component interconnect Special Interest Group (PCI SIG) *PCI Local Bus Specification, Revision 2.2* for 3.3-V operation at 33 or 66 MHz and 32 or 64 bits
 - Support for high-speed external memories, including DDR synchronous dynamic RAM (SDRAM) and ZBT static RAM (SRAM)
 - 16 input and 16 output LVDS channels
 - Direct connection from I/O pins to local interconnect providing fast t_{CO} and t_{SU} times for complex logic
 - MultiVolt I/O support for 1.8-V, 2.5-V, and 3.3-V interfaces
 - Programmable clamp to V_{CCIO}
 - Individual tri-state output enable control for each pin
 - Programmable output slew-rate control to reduce switching noise
 - Support for advanced I/O standards, including low-voltage differential signaling (LVDS), LVPECL, PCI-X, AGP, CTT, SSTL-3 and SSTL-2, GTL+, and HSTL Class I
 - Supports hot-socketing operation
 - Pull-up on I/O pins before and during configuration

Table 2. APEX 20KC Supply Voltages

Feature	Voltage
Internal supply voltage (V_{CCINT})	1.8 V
MultiVolt I/O interface voltage levels (V_{CCIO})	1.8 V, 2.5 V, 3.3 V, 5.0 V (1)

Note:

- (1) APEX 20KC devices can be 5.0-V tolerant by using an external resistor.

Table 7. APEX 20KC Device Features (Part 2 of 2)

Feature	APEX 20KC Devices
I/O standard support	1.8-V, 2.5-V, 3.3-V, 5.0-V I/O 3.3-V PCI and PCI-X 3.3-V AGP CTT GTL+ LVC MOS LV TTL True-LVDS™ and LVPECL data pins (in EP20K400C and larger devices) LVDS and LVPECL clock pins (in all devices) LVDS and LVPECL data pins up to 156 Mbps (in all devices) HSTL Class I PCI-X SSTL-2 Class I and II SSTL-3 Class I and II
Memory support	CAM Dual-port RAM FIFO RAM ROM

All APEX 20KC devices are reconfigurable and are 100% tested prior to shipment. As a result, test vectors do not have to be generated for fault-coverage purposes. Instead, the designer can focus on simulation and design verification. In addition, the designer does not need to manage inventories of different application-specific integrated circuit (ASIC) designs; APEX 20KC devices can be configured on the board for the specific functionality required.

APEX 20KC devices are configured at system power-up with data stored in an Altera serial configuration device or provided by a system controller. Altera offers in-system programmability (ISP)-capable EPC16, EPC2, and EPC1 configuration devices, which configure APEX 20KC devices via a serial data stream. Moreover, APEX 20KC devices contain an optimized interface that permits microprocessors to configure APEX 20KC devices serially or in parallel, and synchronously or asynchronously. The interface also enables microprocessors to treat APEX 20KC devices as memory and configure the device by writing to a virtual memory location, making reconfiguration easy.

The APEX 20KC architecture provides two types of dedicated high-speed data paths that connect adjacent LEs without using local interconnect paths: carry chains and cascade chains. A carry chain supports high-speed arithmetic functions such as counters and adders, while a cascade chain implements wide-input functions such as equality comparators with minimum delay. Carry and cascade chains connect LEs 1 through 10 in an LAB and all LABs in the same MegaLAB structure.

Carry Chain

The carry chain provides a very fast carry-forward function between LEs. The carry-in signal from a lower-order bit drives forward into the higher-order bit via the carry chain, and feeds into both the LUT and the next portion of the carry chain. This feature allows the APEX 20KC architecture to implement high-speed counters, adders, and comparators of arbitrary width. Carry chain logic can be created automatically by the Quartus II Compiler during design processing, or manually by the designer during design entry. Parameterized functions such as DesignWare functions from Synopsys and library of parameterized modules (LPM) functions automatically take advantage of carry chains for the appropriate functions.

The Quartus II Compiler creates carry chains longer than ten LEs by automatically linking LABs together. For enhanced fitting, a long carry chain skips alternate LABs in a MegaLAB structure. A carry chain longer than one LAB skips either from an even-numbered LAB to the next even-numbered LAB, or from an odd-numbered LAB to the next odd-numbered LAB. For example, the last LE of the first LAB in the upper-left MegaLAB structure carries to the first LE of the third LAB in the MegaLAB structure.

Figure 6 shows how an n -bit full adder can be implemented in $n + 1$ LEs with the carry chain. One portion of the LUT generates the sum of two bits using the input signals and the carry-in signal; the sum is routed to the output of the LE. The register can be bypassed for simple adders or used for accumulator functions. Another portion of the LUT and the carry chain logic generates the carry-out signal, which is routed directly to the carry-in signal of the next-higher-order bit. The final carry-out signal is routed to an LE, where it is driven onto the local, MegaLAB, or FastTrack interconnect routing structures.

The counter mode uses two 3-input LUTs: one generates the counter data, and the other generates the fast carry bit. A 2-to-1 multiplexer provides synchronous loading, and another AND gate provides synchronous clearing. If the cascade function is used by an LE in counter mode, the synchronous clear or load overrides any signal carried on the cascade chain. The synchronous clear overrides the synchronous load. LEs in arithmetic mode can drive out registered and unregistered versions of the LUT output.

Clear & Preset Logic Control

Logic for the register's clear and preset signals is controlled by LAB-wide signals. The LE directly supports an asynchronous clear function. The Quartus II Compiler can use a NOT-gate push-back technique to emulate an asynchronous preset or to emulate simultaneous preset and clear or asynchronous load. However, this technique uses three additional LEs per register. All emulation is performed automatically when the design is compiled. Registers that emulate simultaneous preset and load will enter an unknown state upon power-up or when the chip-wide reset is asserted.

In addition to the two clear and preset modes, APEX 20KC devices provide a chip-wide reset pin (DEV_CLRn) that resets all registers in the device. Use of this pin is controlled through an option in the Quartus II software that is set before compilation. The chip-wide reset overrides all other control signals. Registers using an asynchronous preset are preset when the chip-wide reset is asserted; this effect results from the inversion technique used to implement the asynchronous preset.

FastTrack Interconnect

In the APEX 20KC architecture, connections between LEs, ESBs, and I/O pins are provided by the FastTrack interconnect. The FastTrack interconnect is a series of continuous horizontal and vertical routing channels that traverse the device. This global routing structure provides predictable performance, even in complex designs. In contrast, the segmented routing in FPGAs requires switch matrices to connect a variable number of routing paths, increasing the delays between logic resources and reducing performance.

The FastTrack interconnect consists of row and column interconnect channels that span the entire device. The row interconnect routes signals throughout a row of MegaLAB structures; the column interconnect routes signals throughout a column of MegaLAB structures. When using the row and column interconnect, an LE, IOE, or ESB can drive any other LE, IOE, or ESB in a device. See [Figure 9](#).

Figure 10. FastTrack Connection to Local Interconnect

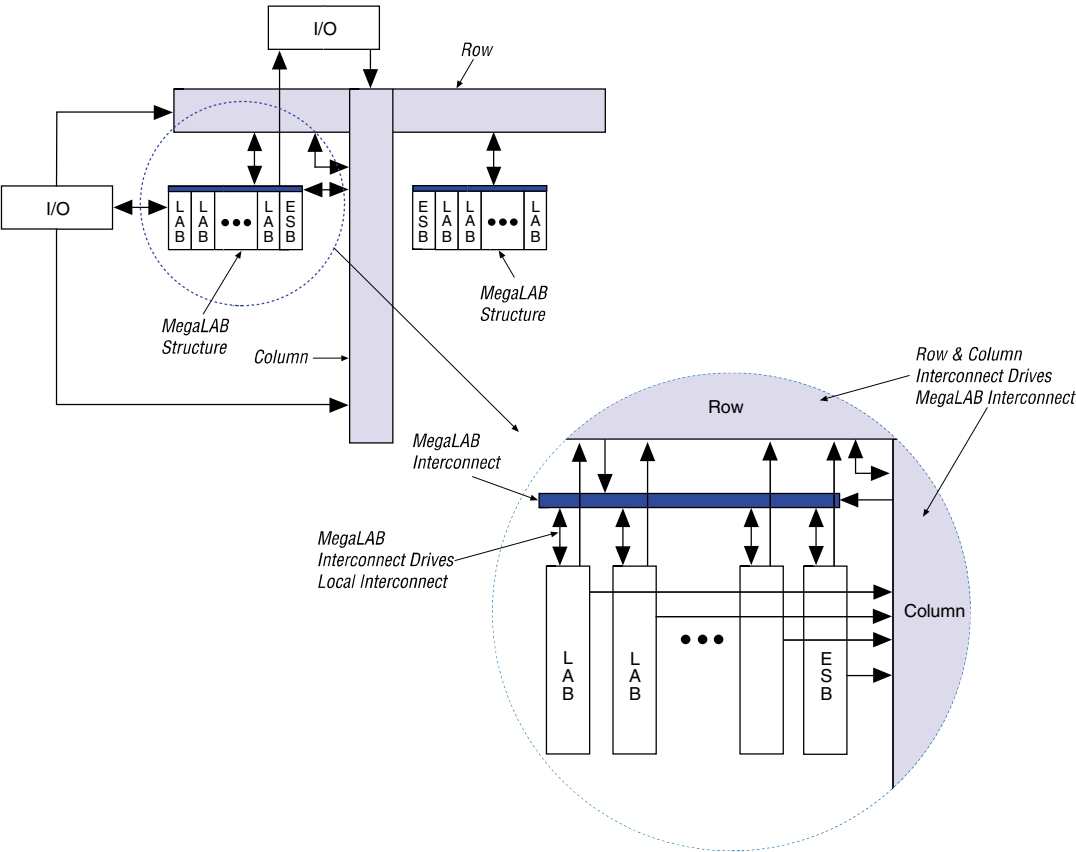
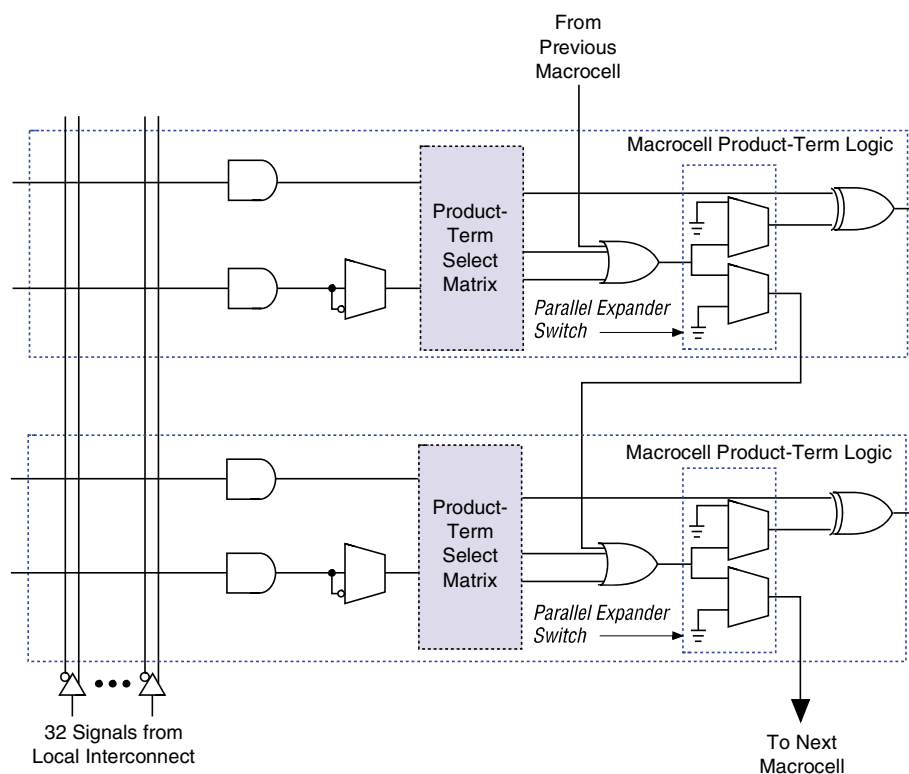


Figure 16. APEX 20KC Parallel Expanders

Embedded System Block

The ESB can implement various types of memory blocks, including dual-port RAM, ROM, FIFO, and CAM blocks. The ESB includes input and output registers; the input registers synchronize writes, and the output registers can pipeline designs to improve system performance. The ESB offers a dual-port mode, which supports simultaneous reads and writes at two different clock frequencies. Figure 17 shows the ESB block diagram.

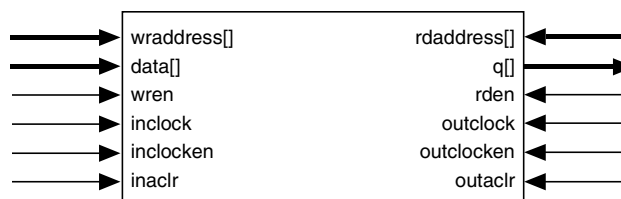
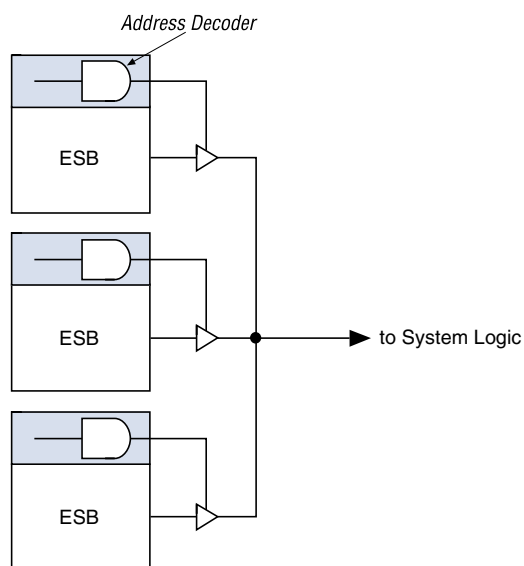
Figure 17. ESB Block Diagram

Figure 18. Deep Memory Block Implemented with Multiple ESBs

The ESB implements two forms of dual-port memory: read/write clock mode and input/output clock mode. The ESB can also be used for bidirectional, dual-port memory applications in which two ports read or write simultaneously. To implement this type of dual-port memory, two ESBs are used to support two simultaneous reads or writes.

The ESB can also use Altera megafunctions to implement dual-port RAM applications where both ports can read or write, as shown in [Figure 19](#).

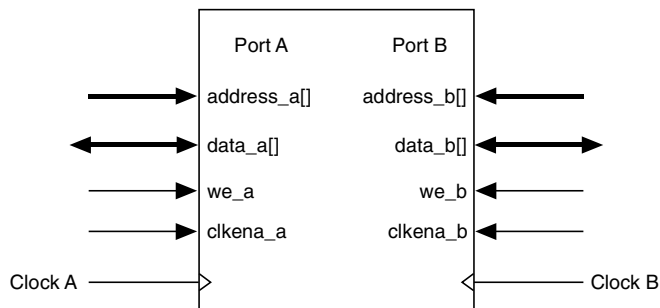
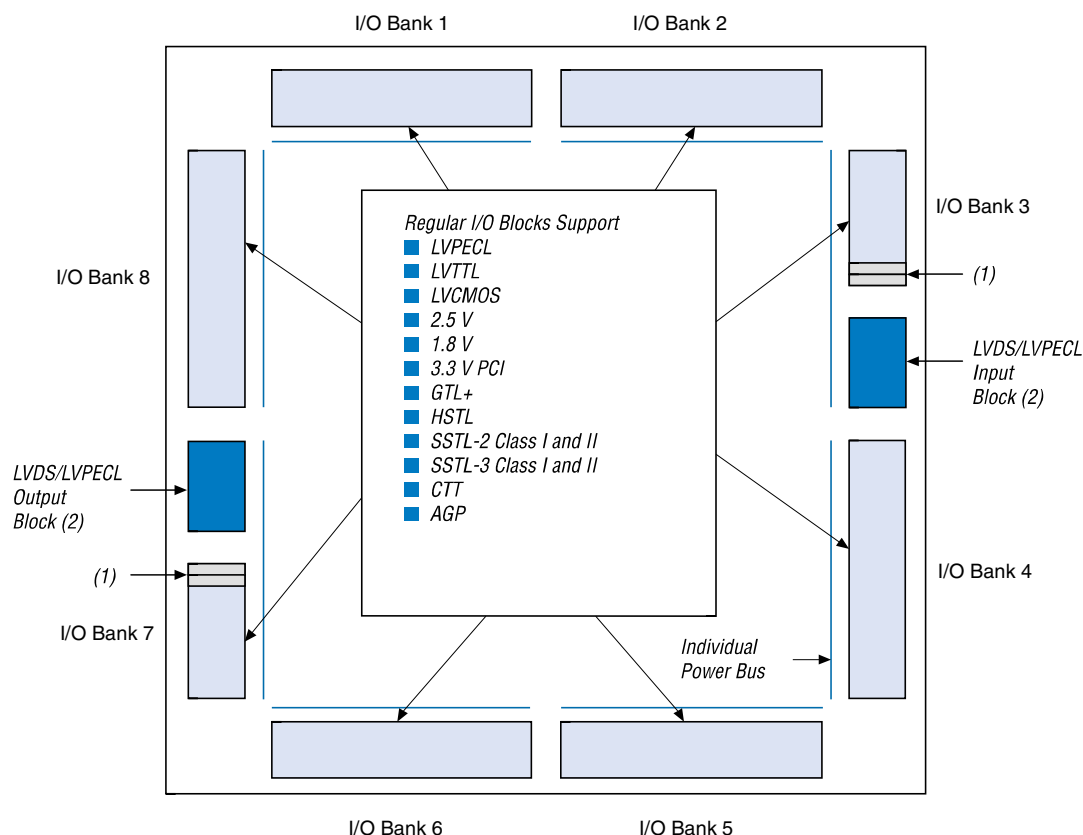
Figure 19. APEX 20KC ESB Implementing Dual-Port RAM

Figure 28. APEX 20KC I/O Banks

**Notes:**

- (1) Any I/O pin within two pads of the LVDS pins can only be used as an input to maintain an acceptable noise level on the V_{CCIO} plane. No output pin can be placed within two pads of LVDS pins unless separated by a power or ground pin. Use the **Show Pads** view in the Quartus II software's Floor Plan Editor to locate these pads. The Quartus II software will give an error message for illegal output or bidirectional pin placement next to the LVDS pin.
- (2) If the LVDS input and output blocks are not used for LVDS, they can support all of the I/O standards and can be used as input, output, or bidirectional pins with V_{CCIO} set to 3.3 V, 2.5 V, or 1.8 V.

Power Sequencing & Hot Socketing

Because APEX 20KC devices can be used in a mixed-voltage environment, they have been designed specifically to tolerate any possible power-up sequence. Therefore, the V_{CCIO} and V_{CCINT} power supplies may be powered in any order.

Table 24. 1.8-V I/O Specifications

Symbol	Parameter	Conditions	Minimum	Maximum	Units
V_{CCIO}	Output supply voltage		1.7	1.9	V
V_{IH}	High-level input voltage		$0.65 \times V_{CCIO}$	$V_{CCIO} + 0.3$	V
V_{IL}	Low-level input voltage			$0.35 \times V_{CCIO}$	V
I_I	Input pin leakage current	$V_{IN} = 0 \text{ V or } 3.3 \text{ V}$	-10	10	μA
V_{OH}	High-level output voltage	$I_{OH} = -2 \text{ mA } (1)$	$V_{CCIO} - 0.45$		V
V_{OL}	Low-level output voltage	$I_{OL} = 2 \text{ mA } (2)$		0.45	V

Table 25. 3.3-V PCI Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		3.0	3.3	3.6	V
V_{IH}	High-level input voltage		$0.5 \times V_{CCIO}$		$V_{CCIO} + 0.5$	V
V_{IL}	Low-level input voltage		-0.5		$0.3 \times V_{CCIO}$	V
I_I	Input pin leakage current	$0 < V_{IN} < V_{CCIO}$	-10		10	μA
V_{OH}	High-level output voltage	$I_{OUT} = -500 \mu\text{A}$	$0.9 \times V_{CCIO}$			V
V_{OL}	Low-level output voltage	$I_{OUT} = 1,500 \mu\text{A}$			$0.1 \times V_{CCIO}$	V

Table 26. 3.3-V PCI-X Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	Output supply voltage		3.0	3.3	3.6	V
V_{IH}	High-level input voltage		$0.5 \times V_{CCIO}$		$V_{CCIO} + 0.5$	V
V_{IL}	Low-level input voltage		-0.5		$0.35 \times V_{CCIO}$	V
V_{IPU}	Input pull-up voltage		$0.7 \times V_{CCIO}$			V
I_{IL}	Input pin leakage current	$0 < V_{IN} < V_{CCIO}$	-10.0		10.0	μA
V_{OH}	High-level output voltage	$I_{OUT} = -500 \mu A$	$0.9 \times V_{CCIO}$			V
V_{OL}	Low-level output voltage	$I_{OUT} = 1500 \mu A$			$0.1 \times V_{CCIO}$	V
L_{pin}	Pin Inductance				15.0	nH

Table 27. 3.3-V LVDS I/O Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		3.135	3.3	3.465	V
V_{OD}	Differential output voltage	$R_L = 100 \Omega$	250		450	mV
ΔV_{OD}	Change in VOD between high and low	$R_L = 100 \Omega$			50	mV
V_{OS}	Output offset voltage	$R_L = 100 \Omega$	1.125	1.25	1.375	V
ΔV_{OS}	Change in VOS between high and low	$R_L = 100 \Omega$			50	mV
V_{TH}	Differential input threshold	$V_{CM} = 1.2 V$	-100		100	mV
V_{IN}	Receiver input voltage range		0.0		2.4	V
R_L	Receiver differential input resistor (external to APEX devices)		90	100	110	Ω

Table 28. GTL+ I/O Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{TT}	Termination voltage		1.35	1.5	1.65	V
V_{REF}	Reference voltage		0.88	1.0	1.12	V
V_{IH}	High-level input voltage		$V_{REF} + 0.1$			V
V_{IL}	Low-level input voltage				$V_{REF} - 0.1$	V
V_{OL}	Low-level output voltage	$I_{OL} = 36 \text{ mA}$ (2)			0.65	V

Table 29. SSTL-2 Class I Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		2.375	2.5	2.625	V
V_{TT}	Termination voltage		$V_{REF} - 0.04$	V_{REF}	$V_{REF} + 0.04$	V
V_{REF}	Reference voltage		1.15	1.25	1.35	V
V_{IH}	High-level input voltage		$V_{REF} + 0.18$		$V_{CCIO} + 0.3$	V
V_{IL}	Low-level input voltage		-0.3		$V_{REF} - 0.18$	V
V_{OH}	High-level output voltage	$I_{OH} = -7.6 \text{ mA}$ (1)	$V_{TT} + 0.57$			V
V_{OL}	Low-level output voltage	$I_{OL} = 7.6 \text{ mA}$ (2)			$V_{TT} - 0.57$	V

Table 34. LVPECL Specifications

Symbol	Parameter	Minimum	Typical	Maximum	Units
V_{CCIO}	Output Supply Voltage	3.135	3.3	3.465	V
V_{IH}	Low-level input voltage	1300		1700	mV
V_{IL}	High-level input voltage	2100		2600	mV
V_{OH}	Low-level output voltage	1450		1650	mV
V_{OL}	High-level output voltage	2275		2420	mV
V_{ID}	Input voltage differential	400	600	950	mV
V_{OD}	Output voltage differential	625	800	950	mV
t_r, t_f	Rise/fall time (20 to 80%)	85		325	ps
t_{DSKEW}	Differential skew			25	ps
t_O	Output load		150		Ω
R_L	Receiver differential input resistor		100		Ω

Table 35. 3.3-V AGP I/O Specifications

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V_{CCIO}	I/O supply voltage		3.15	3.3	3.45	V
V_{REF}	Reference voltage		$0.39 \times V_{CCIO}$		$0.41 \times V_{CCIO}$	V
V_{IH}	High-level input voltage		$0.5 \times V_{CCIO}$		$V_{CCIO} + 0.5$	V
V_{IL}	Low-level input voltage				$0.3 \times V_{CCIO}$	V
V_{OH}	High-level output voltage	$I_{OUT} = -500 \mu A$	$0.9 \times V_{CCIO}$		3.6	V
V_{OL}	Low-level output voltage	$I_{OUT} = 1500 \mu A$			$0.1 \times V_{CCIO}$	V
I_I	Input pin leakage current	$0 < V_{IN} < V_{CCIO}$	-10		10	μA

Table 38. APEX 20KC t_{MAX} ESB Timing Parameters

Symbol	Parameter
t_{ESBARC}	ESB asynchronous read cycle time
t_{ESBSRC}	ESB synchronous read cycle time
t_{ESBAWC}	ESB asynchronous write cycle time
t_{ESBSWC}	ESB synchronous write cycle time
$t_{ESBWASU}$	ESB write address setup time with respect to WE
t_{ESBWAH}	ESB write address hold time with respect to WE
$t_{ESBWDSU}$	ESB data setup time with respect to WE
t_{ESBWDH}	ESB data hold time with respect to WE
$t_{ESBRASU}$	ESB read address setup time with respect to RE
t_{ESBRAH}	ESB read address hold time with respect to RE
$t_{ESBWESU}$	ESB WE setup time before clock when using input register
$t_{ESBDATASU}$	ESB data setup time before clock when using input register
$t_{ESBWADDRSU}$	ESB write address setup time before clock when using input registers
$t_{ESBRADDRSU}$	ESB read address setup time before clock when using input registers
$t_{ESBDATAO1}$	ESB clock-to-output delay when using output registers
$t_{ESBDATAO2}$	ESB clock-to-output delay without output registers
t_{ESBDD}	ESB data-in to data-out delay for RAM mode
t_{PD}	ESB macrocell input to non-registered output
$t_{PTERMSU}$	ESB macrocell register setup time before clock
$t_{PTERMCO}$	ESB macrocell register clock-to-output delay

Table 39. APEX 20KC t_{MAX} Routing Delays

Symbol	Parameter
t_{F1-4}	Fan-out delay estimate using local interconnect
t_{F5-20}	Fan-out delay estimate using MegaLab interconnect
t_{F20+}	Fan-out delay estimate using FastTrack interconnect

Table 42. APEX 20KC External Bidirectional Timing Parameters *Note (1)*

Symbol	Parameter	Condition
$t_{\text{INSUBIDIR}}$	Setup time for bidirectional pins with global clock at LAB-adjacent input register	
t_{INHBIDIR}	Hold time for bidirectional pins with global clock at LAB-adjacent input register	
$t_{\text{OUTCOBIDIR}}$	Clock-to-output delay for bidirectional pins with global clock at IOE register	C1 = 35 pF
t_{XZBIDIR}	Synchronous output enable register to output buffer disable delay	C1 = 35 pF
t_{ZXBIDIR}	Synchronous output enable register to output buffer enable delay	C1 = 35 pF
$t_{\text{INSUBIDIRPLL}}$	Setup time for bidirectional pins with PLL clock at LAB-adjacent input register	
$t_{\text{INHBIDIRPLL}}$	Hold time for bidirectional pins with PLL clock at LAB-adjacent input register	
$t_{\text{OUTCOBIDIRPLL}}$	Clock-to-output delay for bidirectional pins with PLL clock at IOE register	C1 = 35 pF
$t_{\text{XZBIDIRPLL}}$	Synchronous output enable register to output buffer disable delay with PLL	C1 = 35 pF
$t_{\text{ZXBIDIRPLL}}$	Synchronous output enable register to output buffer enable delay with PLL	C1 = 35 pF

Note to tables:

(1) These timing parameters are sample-tested only.

Tables 43 through 78 show the f_{MAX} and external timing parameters for EPC20K100C, EPC20K200C, EP20K400C, EP20K600C, EP20K1000C, and EP20K1500C devices.

Table 43. EP20K100C f_{MAX} LE Timing Parameters *Note (1)*

Symbol	-7 Speed Grade		-8 Speed Grade (2)		-9 Speed Grade (2)		Unit
	Min	Max	Min	Max	Min	Max	
t_{SU}	0.3						ns
t_H	0.3						ns
t_{CO}		0.3					ns
t_{LUT}		0.7					ns

Table 44. EP20K100C f_{MAX} ESB Timing Parameters *Note (1)*

Symbol	-7 Speed Grade		-8 Speed Grade (2)		-9 Speed Grade (2)		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.4					ns
t_{ESBSRC}		2.5					ns
t_{ESBAWC}		3.1					ns
t_{ESBSWC}		3.0					ns
$t_{ESBWASU}$	0.5						ns
t_{ESBWAH}	0.5						ns
$t_{ESBWDSU}$	0.6						ns
t_{ESBWDH}	0.5						ns
$t_{ESBRASU}$	1.4						ns
t_{ESBRAH}	0.0						ns
$t_{ESBWESU}$	2.3						ns
$t_{ESBDATASU}$	0.0						ns
$t_{ESBWADDRSU}$	0.2						ns
$t_{ESBRADDRSU}$	0.2						ns
$t_{ESBDATACO1}$		1.0					ns
$t_{ESBDATACO2}$		2.3					ns
t_{ESBDD}		2.7					ns
t_{PD}		1.6					ns
$t_{PTERMSU}$	1.0						ns
$t_{PTERMCO}$		1.0					ns

Table 50. EP20K200C t_{MAX} ESB Timing Parameters *Note (1)*

Symbol	-7 Speed Grade		-8 Speed Grade (2)		-9 Speed Grade (2)		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.4					ns
t_{ESBSRC}		2.5					ns
t_{ESBAWC}		3.1					ns
t_{ESBSWC}		3.0					ns
$t_{ESBWASU}$	0.5						ns
t_{ESBWAH}	0.5						ns
$t_{ESBWDSU}$	0.6						ns
t_{ESBWDH}	0.5						ns
$t_{ESBRASU}$	1.4						ns
t_{ESBRAH}	0.0						ns
$t_{ESBWESU}$	2.3						ns
$t_{ESBDATASU}$	0.0						ns
$t_{ESBWADDRSU}$	0.2						ns
$t_{ESBRADDRSU}$	0.2						ns
$t_{ESBDATACO1}$		1.0					ns
$t_{ESBDATACO2}$		2.3					ns
t_{ESBDD}		2.7					ns
t_{PD}		1.6					ns
$t_{PTERMSU}$	1.0						ns
$t_{PTERMCO}$		1.0					ns

Table 51. EP20K200C t_{MAX} Routing Delays *Note (1)*

Symbol	-7 Speed Grade		-8 Speed Grade (2)		-9 Speed Grade (2)		Unit
	Min	Max	Min	Max	Min	Max	
t_{F1-4}	0.2						ns
t_{F5-20}	0.9						ns
t_{F20+}	1.0						ns

Table 64. EP20K600C Minimum Pulse Width Timing Parameters *Note (1)*

Symbol	-7 Speed Grade		-8 Speed Grade (2)		-9 Speed Grade (2)		Unit
	Min	Max	Min	Max	Min	Max	
t_{CH}	2.3						ns
t_{CL}	2.3						ns
t_{CLRP}	0.2						ns
t_{PREP}	0.2						ns
t_{ESBCH}	2.3						ns
t_{ESBCL}	2.3						ns
t_{ESBWP}	1.1						ns
t_{ESBRP}	0.9						ns

Table 65. EP20K600C External Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade (2)		-9 Speed Grade (2)		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.2						ns
t_{INH}	0.0						ns
t_{OUTCO}	2.0	5.0					ns
$t_{INSUPLL}$	3.3						ns
t_{INHPLL}	0.0						ns
$t_{OUTCOPLL}$	0.5	2.1					ns

Table 68. EP20K1000C f_{MAX} ESB Timing Parameters *Note (1)*

Symbol	-7 Speed Grade		-8 Speed Grade (2)		-9 Speed Grade (2)		Unit
	Min	Max	Min	Max	Min	Max	
t_{ESBARC}		1.3					ns
t_{ESBSRC}		2.3					ns
t_{ESBAWC}		2.9					ns
t_{ESBSWC}		2.7					ns
$t_{ESBWASU}$	0.4						ns
t_{ESBWAH}	0.4						ns
$t_{ESBWDSU}$	0.5						ns
t_{ESBWDH}	0.4						ns
$t_{ESBRASU}$	1.3						ns
t_{ESBRAH}	0.0						ns
$t_{ESBWESU}$	2.0						ns
$t_{ESBDATASU}$	0.0						ns
$t_{ESBWADDRSU}$	0.1						ns
$t_{ESBRADDRSU}$	0.1						ns
$t_{ESBDATACO1}$		1.0					ns
$t_{ESBDATACO2}$		2.0					ns
t_{ESBDD}		2.4					ns
t_{PD}		1.4					ns
$t_{PTERMSU}$	0.9						ns
$t_{PTERMCO}$		1.0					ns

Table 69. EP20K1000C f_{MAX} Routing Delays *Note (1)*

Symbol	-7 Speed Grade		-8 Speed Grade (2)		-9 Speed Grade (2)		Unit
	Min	Max	Min	Max	Min	Max	
t_{F1-4}	0.2						ns
t_{F5-20}	1.3						ns
t_{F20+}	2.6						ns

Table 76. EP20K1500C Minimum Pulse Width Timing Parameters *Note (1)*

Symbol	-7 Speed Grade		-8 Speed Grade (2)		-9 Speed Grade (2)		Unit
	Min	Max	Min	Max	Min	Max	
t_{CH}	2.0						ns
t_{CL}	2.0						ns
t_{CLRP}	0.2						ns
t_{PREP}	0.2						ns
t_{ESBCH}	2.0						ns
t_{ESBCL}	2.0						ns
t_{ESBWP}	1.0						ns
t_{ESBRP}	0.8						ns

Table 77. EP20K1500C External Timing Parameters

Symbol	-7 Speed Grade		-8 Speed Grade (2)		-9 Speed Grade (2)		Unit
	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.1						ns
t_{INH}	0.0						ns
t_{OUTCO}	2.0	5.0					ns
$t_{INSUPLL}$	3.2						ns
t_{INHPLL}	0.0						ns
$t_{OUTCOPLL}$	0.5	2.1					ns



101 Innovation Drive
San Jose, CA 95134
(408) 544-7000
<http://www.altera.com>
Applications Hotline:
(800) 800-EPLD
Customer Marketing:
(408) 544-7104
Literature Services:
lit_req@altera.com

Copyright © 2001 Altera Corporation. All rights reserved. AMPP, Altera, APEX, APEX 20K, APEX 20KC, APEX 20KE, ByteBlasterMV, ClockBoost, ClockLock, ClockShift, FastRow, FastTrack, FineLine BGA, MasterBlaster, MegaCore, MegaLAB, MultiCore, MultiVolt, NativeLink, Quartus, Quartus II, SignalTap, True-LVDS, Turbo Bit, and specific device designations are trademarks and/or service marks of Altera Corporation in the United States and other countries. Altera acknowledges the trademarks of other organizations for their respective products or services mentioned in this document. Altera products are protected under numerous U.S. and foreign patents and pending applications, maskwork rights, and copyrights. Altera warrants performance of its semiconductor products to current specifications in accordance with Altera's standard warranty, but reserves the right to make changes to any products and services at any time without notice. Altera assumes no responsibility or liability arising out of the application or use of any information, product, or service described herein except as expressly agreed to in writing by Altera Corporation. Altera customers are advised to obtain the latest version of device specifications before relying on any published information and before placing orders for products or services.

